1 Number	Hits	Rearch Text	DR	277 1 44
	1730	thigh near (dielectric insulat03, near	USPAT;	Time stamp 2003/01/21 1 :33
		<pre>% f.Starty.fi.</pre>	DO-FGFOR;	
			EPO; JPO; DEPWENT;	
			IRM TILE	
e.	184	Thigh near (dielectric insulates, near	USPĀT;	2603/01/21 10:36
		"Gastant .ti.) and Tran cavity mostly	US-PGPUB;	2272, 3177,1 1,7:55
		opening recess trench)	EPO; JFO;	
			DERWENT;	
3	150	((Thigh near (dielectric insulat\$3) near	IPM_TDB U.PAT;	2002/02/03
		Constant).ti.) and (gap cavity groove	U.'-PGPUB;	2003/01/21 10:48
		opening recess trench)) and (substrate	E: ); JPO;	
		wafer pad base)	DERWENT;	
4	122	((((high near (dielectric insulat\$3) near	IFH_TDB	
		constant).ti.) and (gap cavity groove	CEPAT; CE-PGPUB;	2003/01/21 09:54
		opening recess trench)) and (substrate	El 1; JPO;	
		wafer pad base)) and @ad<20000526	DEFWENT;	
ŗ,	6.4		1F::_TDB	
Č	74	<pre>((((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove</pre>	US! AT;	2003/01/21 10:10
		opening recess trench); and (substrate	US PGPUB; EF; JPO;	
		wafer pad base)) and @ad<20000526) and	DEFWENT;	
6		Capacitor	IEN TOB	
,	25	(((((high near (dielectric insulat\$3)	USIĀT;	2003/01/21 10:10
		near constant).ti.; and (gap cavity groove opening recess trench); and (substrate	US - PGPUB;	
		wafer pad base)) and @ad<20000526) and	EF ; JPO; DEFWENT;	
		capacitor) and conductor	IB:: TDB	
~7	43095	high near (dielectric insulat\$3 K)	U3:ĀT;	2003/01/21 10:34
			U3-PGPUB;	
			EP ; JPO;	
			DEFWENT; 1811 TDB	
ş	16877	(high near (dielectric insulat\$3 K:) and	US!AT;	2003/01/21 10:41
		(gap cavity groove opening recess trench)	US-PGPUB;	1000,01,01 10.11
			EP ; JPO;	
			DEFWENT; IBN: TDB	
9	1656	((high near (dielectric insulat\$3 K)) and	US:AT;	2003/01/21 10:45
		(gap cavity groove opening recess trench)	US PGPUB;	2003/02/21 10.43
		and (interlayer (inter near1 layer))	EP:; JPO;	
			DEL VENT;	
10	1624	((high near (dielectric insulat\$3 K)) and	IEN TDB USLĀT;	2903/01/21 10:47
		(gap cavity groove opening recess trench))	US-PGPUB;	2003/01/21 10:47
		and (interlayer (inter nearl layer))) and	EF(; JPO;	
		'metal wir\$3 conduct\$3)	DELWENT;	
	992	. high near (dielectric insulat83 K):	IBM_TDB USPAT:	0000 /01 /02 10 10
		and rap cavity groupe opening rowers	US-PSFUE;	2003/01/21 10:47
		trendid and ( nterlayer inter hear)	EPO; IPO;	
		layer _ and .meral wirs conducts3., and	DEPWENT;	
·	49.1	<pre>capabitor *()high near (dielectric insulut\$3 k)</pre>	IBM_TDB	
	. 1	and Tap davity groove opening recess	USFĀT; US-PGPUB;	2003/01/21 10:48
		trench); and (interlayer (inter near)	EPO; JPO;	
		layer);; and (metal wir\$3 conduct\$3)) and	DEPWENT;	
		papabitor) and (substrate wafer pad base)	IBM_TDB	